Silicon PNP Power Transistors 2SA1329

DESCRIPTION

- With TO-220 package
- Complement to type 2SC3346
- Low collector saturation voltage
- High speed switching time

APPLICATIONS

- High current switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

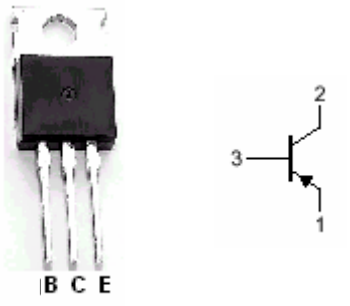

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-12	A
I_B	Base current		-2	A
P_C	Collector power dissipation	T_C=25℃	40	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA ,I_B=0	-80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-6A; I_B=-0.3A		-0.2	-0.4	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-6A; I_B=-0.3A		-0.9	-1.2	V
I_{CBO}	Collector cut-off current	V_{CB}=-80V; I_E=0			-10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-10	μA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-1V	70		240	
h_{FE-2}	DC current gain	I_C=-6A ; V_{CE}=-1V	40			
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=-10V;f=1MHz		400		pF
f_T	Transition frequency	I_C=-1A ; V_{CE}=-5V		50		MHz
Switching times						
t_{on}	Turn-on time	I_{B1}=- I_{B2}=-0.3A R_L=5Ω;V_{CC}=-30V		0.3		μs
t_s	Storage time			1.0		μs
t_f	Fall time			0.5		μs

◆ **h_{FE-1} Classifications**

O	Y
70-140	120-240

PACKAGE OUTLINE

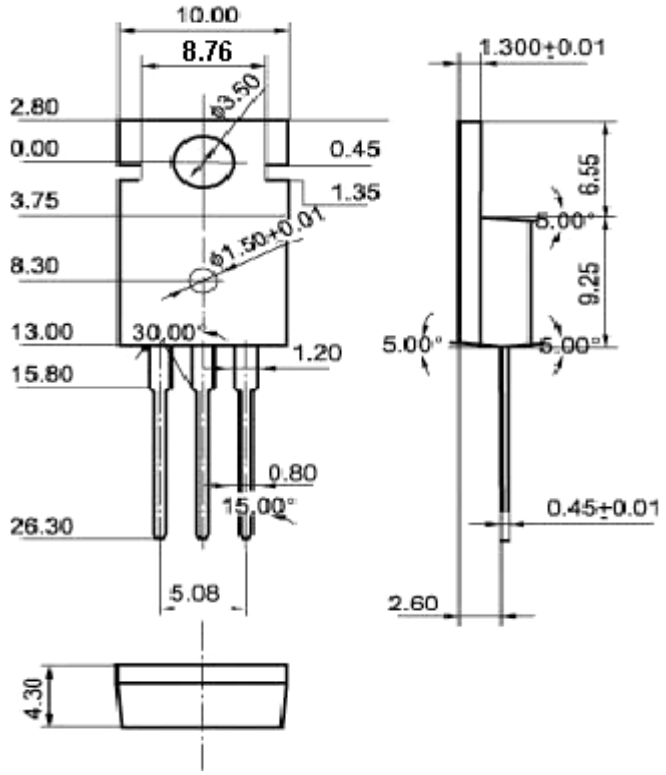

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)

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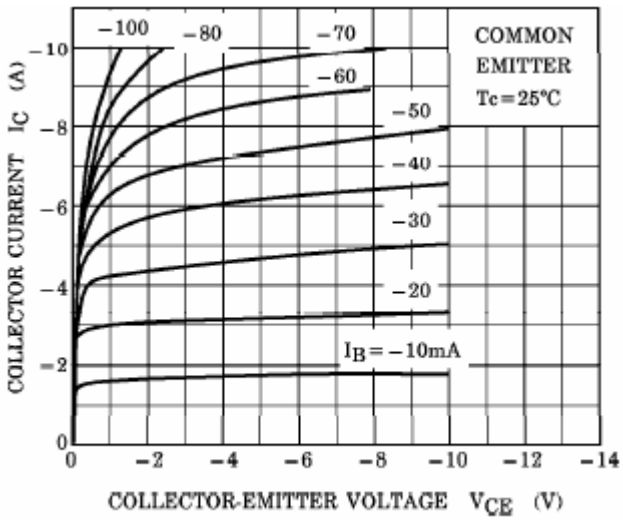

Fig.3 Static Characteristic

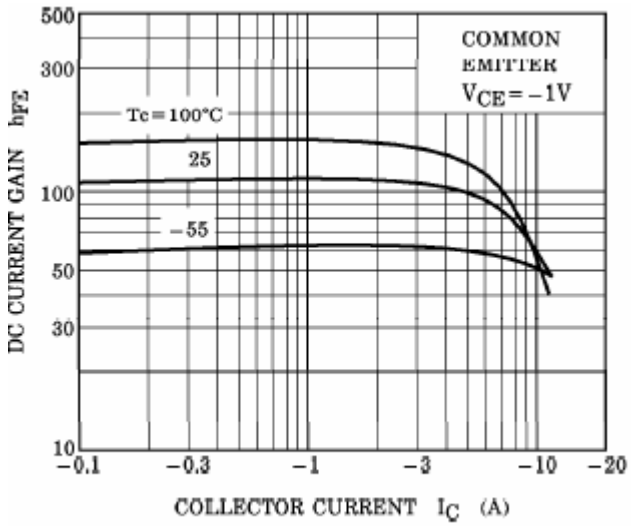

Fig.4 DC current Gain

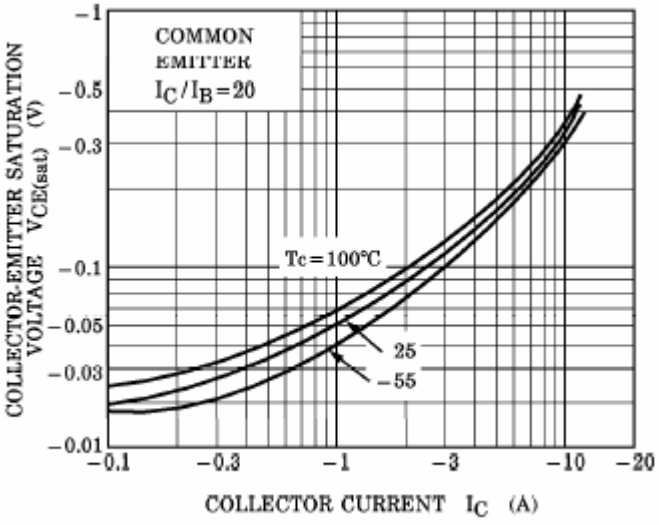

Fig.5 Collector-Emitter Saturation Voltage

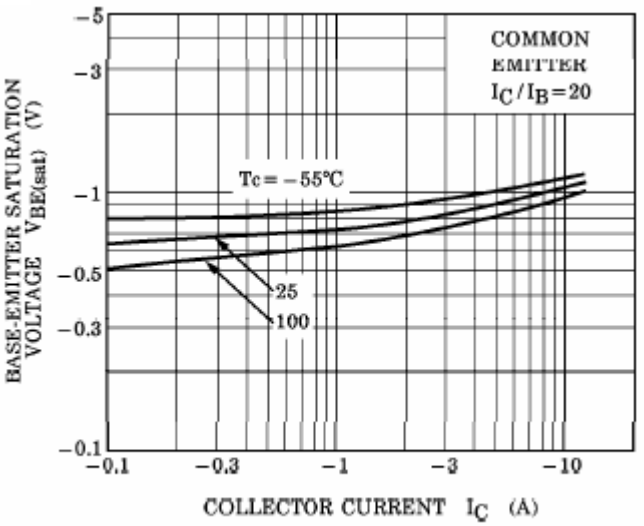

Fig.6 Base-Emitter Saturation Voltage

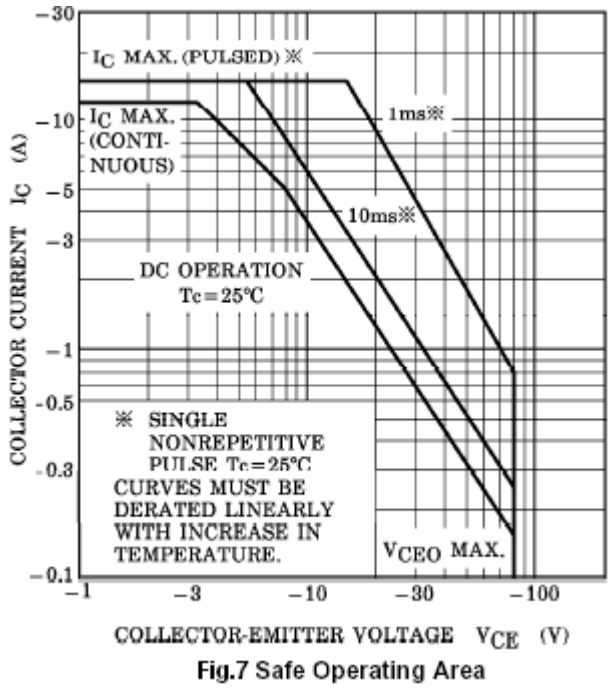

Fig.7 Safe Operating Area